



Pushing the mobility limits on 4" MBE systems

SAND2013-8364C

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Sandia National Laboratories**

NAMBE 2013

The Art of MBE Workshop

Oct. 10, 2013, Banff, Canada



This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S. Department of Energy, Office of Basic Energy Sciences user facility. Sandia National Laboratories is a multi-program laboratory managed and operated by Sandia Corporation, a wholly owned subsidiary of Lockheed Martin Corporation, for the U.S. Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.





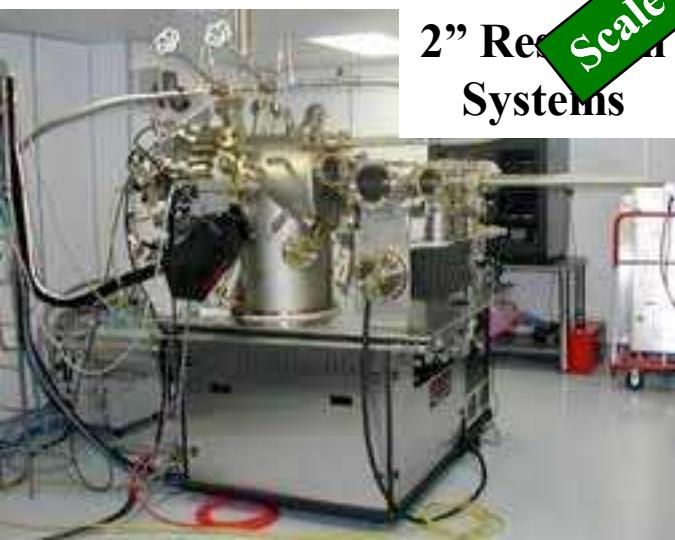
Production
systems

Scale Down

4" MBE

2" Research
Systems

Scale Up





Strength & Weaknesses

- 2" Characteristics
 - Small, Compact
 - Short source-substrate dis.
 - Smaller cells

2" Strengths

- **Less Space**
- **Less Cost**
- **Lower cell temp**
- **Lower heat load**
- **Quicker adjustments**
- **Quicker stabilization**

2" Weaknesses

- **Fewer, smaller ports**
 - Cells & others
- **Small growth area**
- **Poor uniformity**
- **Small material capacity**
- **Poor flux stability w/time**



Strength & Weaknesses

- Production Characteristics
 - Large size
 - Big substrate-source dis.
 - Big cells

Production Strengths

- **More, larger ports**
 - Cells & others
- **Large growth area**
- **Excellent uniformity**
- **Large material capacity**
- **Good flux stability w/time**

Production Weaknesses

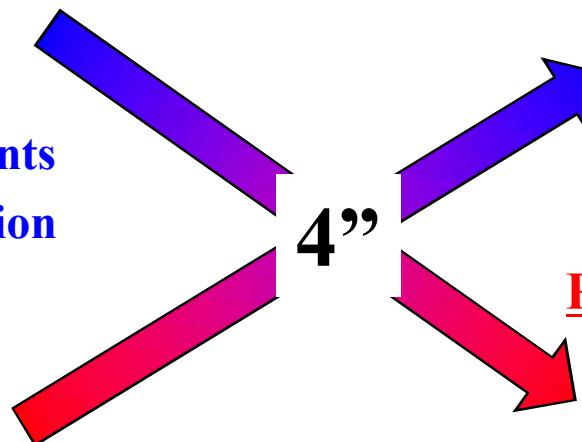
- **Large Space**
- **Large Cost**
- **Higher cell temp**
- **Large heat load**
- **Larger material consumption**
- **Slower adjustments**
- **Longer stabilization**



Interesting Note

2" Strengths

- Less Space
- Less Cost
- Lower cell temp
- Lower heat load
- Quicker adjustments
- Quicker stabilization



2" Weaknesses

- Fewer, smaller ports
 - Cells & others
- Small growth area
- Poor uniformity
- Small material capacity
- Poor flux stability w/time

Production Strengths

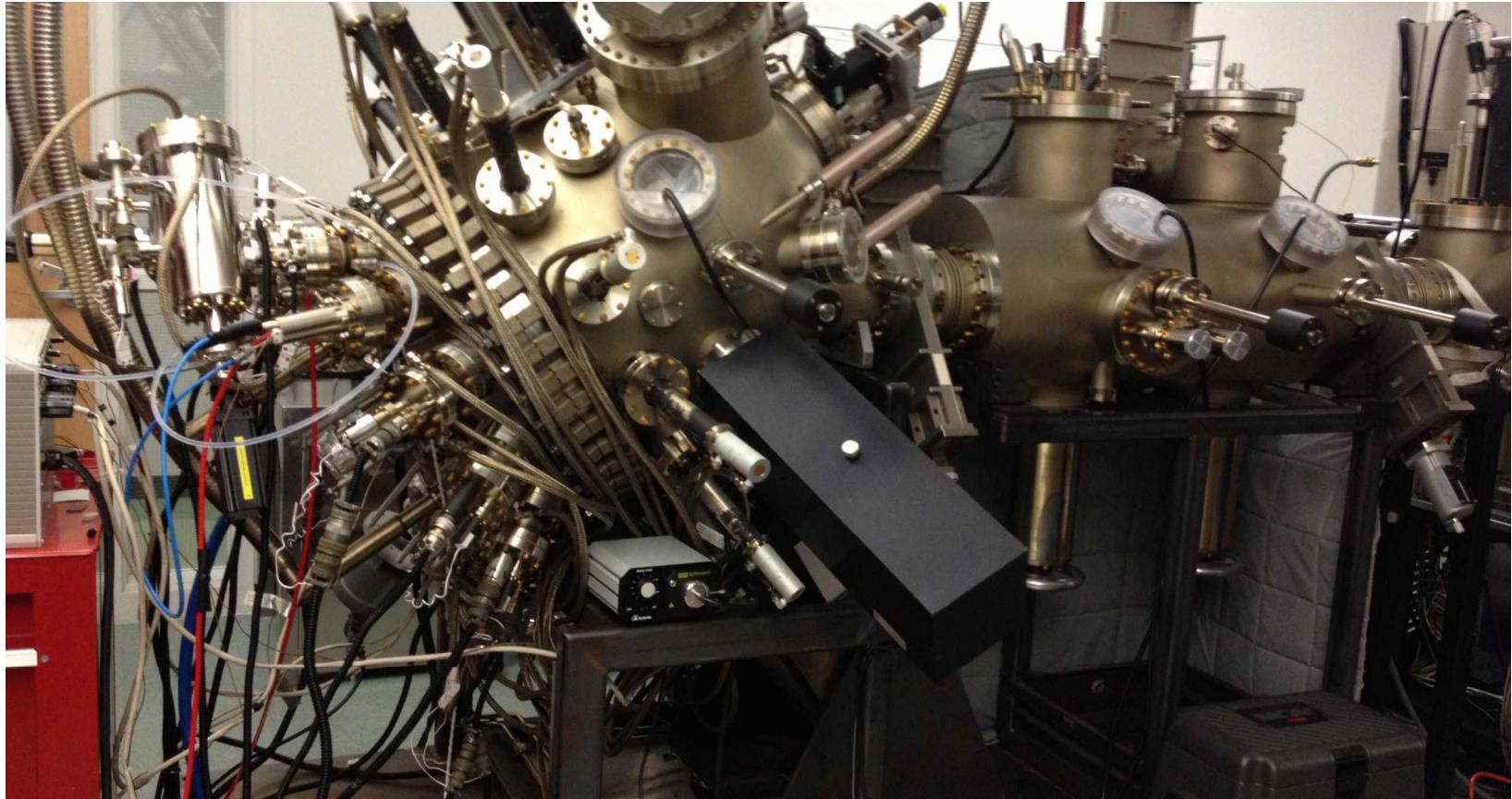
- More, larger ports
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Production Weaknesses

- Large Space
- Large Cost
- Higher cell temp
- Large heat load
- Larger material consumption
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- Longer stabilization



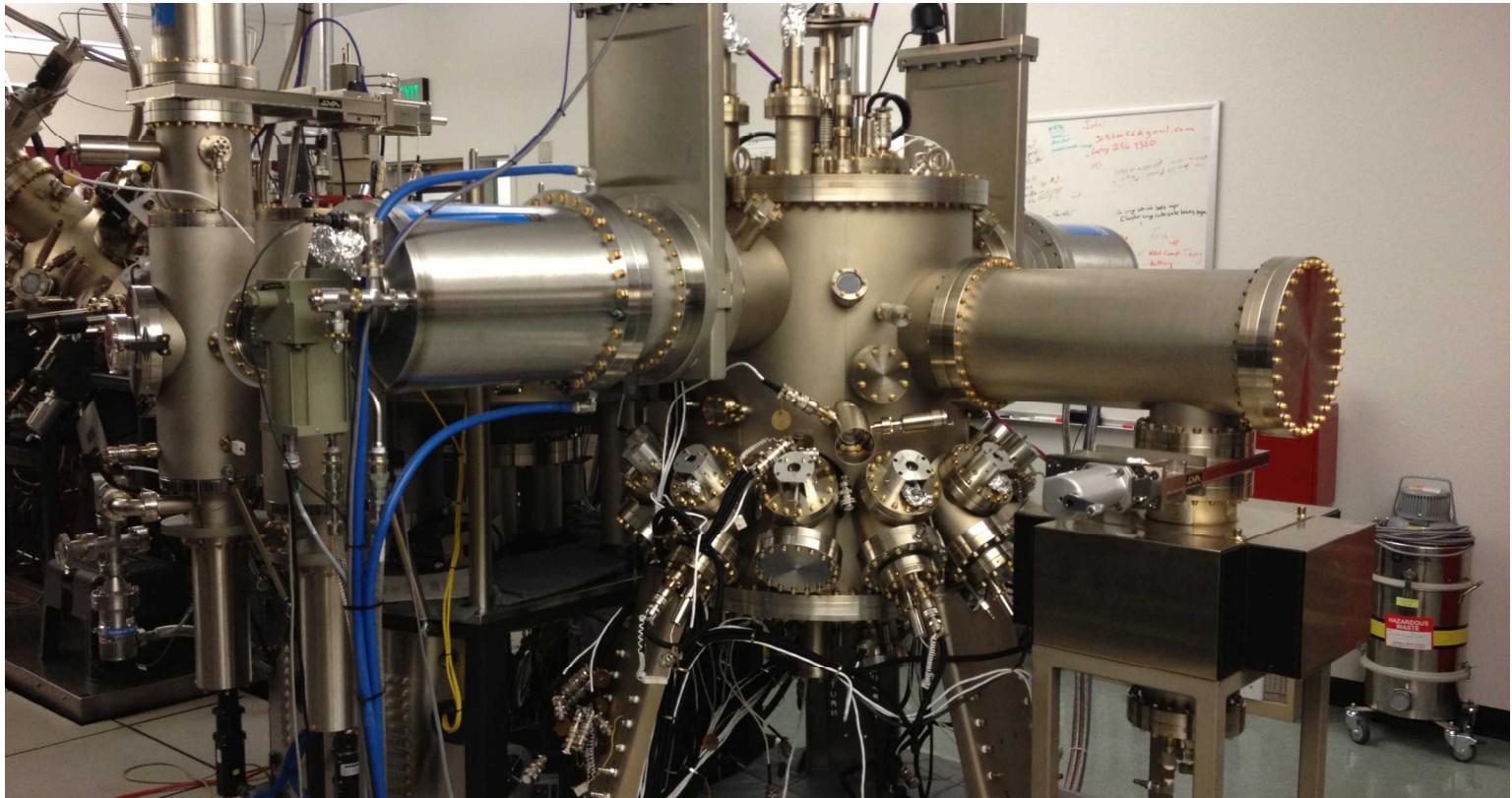
My Lab



EPI 1240: ~Research



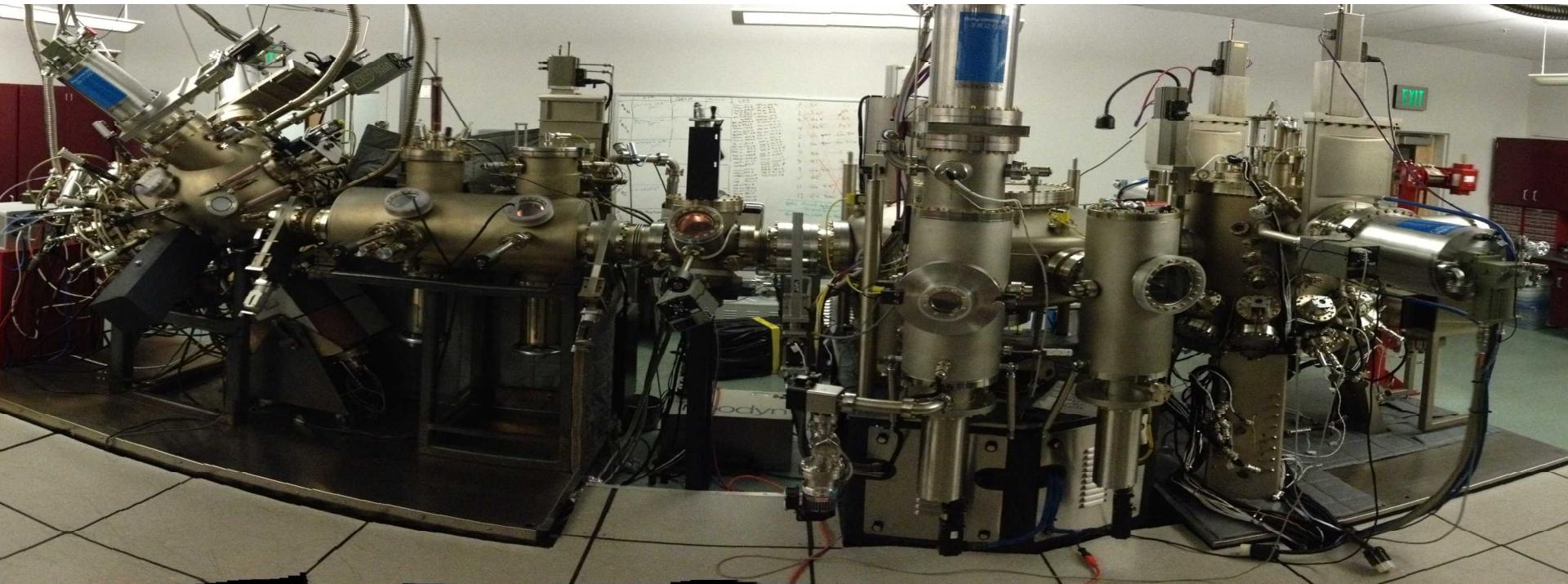
My Lab



Veeco GEN20: ~Production
Scaled down GEN2000



My Lab





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Molecular Foundry
Lawrence Berkeley National Laboratory



Center for Nanoscale Materials
Argonne National Laboratory



Center for Functional Nanomaterials
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Center for Integrated Nanotechnologies
Los Alamos National Laboratory &
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CINT is a DOE/BES National User Facility

- Access via competitive system based on scientific quality
- No-fee for pre-competitive research (Jointly owned IP)
- Full-cost recovery required for proprietary research (User owns IP)
- Collaborative research or just access equipment
- Flexible project duration, 18 month maximum, renewable
- Semi-Annual Call for User Proposals (March/September)
- Rapid Access Proposals for off-cycle, urgent research
- CINT cannot provide funding to users

For More Information:

<http://CINT.lanl.gov>



MBE at a User Facility?

- Access via competitive system based on scientific quality
- Also judged on feasibility
- Users don't actually run the machine themselves
- This past fiscal year – 40 User Projects
- Projects can be grouped
 - “High” mobility 2D electrons and holes for transport
 - Require high purity, reasonable precision.
 - Quantum cascade laser (QCL) primarily in THz
 - Require high precision, somewhat high purity
 - Other optical emitters and detectors
- All structures can be grown in either machine
 - BUT there is a preferred machine
 - => Nitty-gritty of using/designing 4" machines



What limits mobility in 4” compared to 2”?

- Bulk Crystal Quality
 - Defects, interface roughness...
- Impurities
 - Intentional
 - Structure
 - Unintentional
 - Source material
 - MBE system
 - Design, cells, heat load

Size Independent

Size Dependent



Source Flange Design

<u>Design</u>	<u>1240</u>	<u>GEN20</u>	
Cell Port #	12	12	
Cell Port Size	4.5"	4.5"	
Angle from Normal	34°	45°	
Source-Substrate Distance	10.55"	11.0"	=> Cells run hotter than 2"
<u>Consequences</u>			
Uniformity	±0.55%	±0.15%	



Material Consumption ($\mu\text{m/g}$)

<u>Cell Type</u>	<u>1240</u>	<u>GEN20</u>
Ga 85cc (w/insert)	3.2	2.6
Ga Sumo (400g)	-	1.8
AS (Mark IV)	0.9	0.6

This affects:

- Length of campaign => material purity**
- Cell stability during long growths**

Ga Load (g) 600-700 1600



Ga Cell Choice

<u>Type</u>	<u>Load (g)</u>	<u>Backgrnd (/cc)</u>	<u>am Stabilize (hr)</u>	<u>Step Stabilize (min)</u>
85cc w/insert	125	<upper e12	~0.5	10-15
Sumo 400g	350	mid e13	1-2	30-60
Sumo 900g	650	mid e13	3-4	don't bother

Consequences:

- .HiMo -> 85**
- .QCLs -> Sumo**

- Don't change Sumo, set other to it**
- Run 24hr during week**

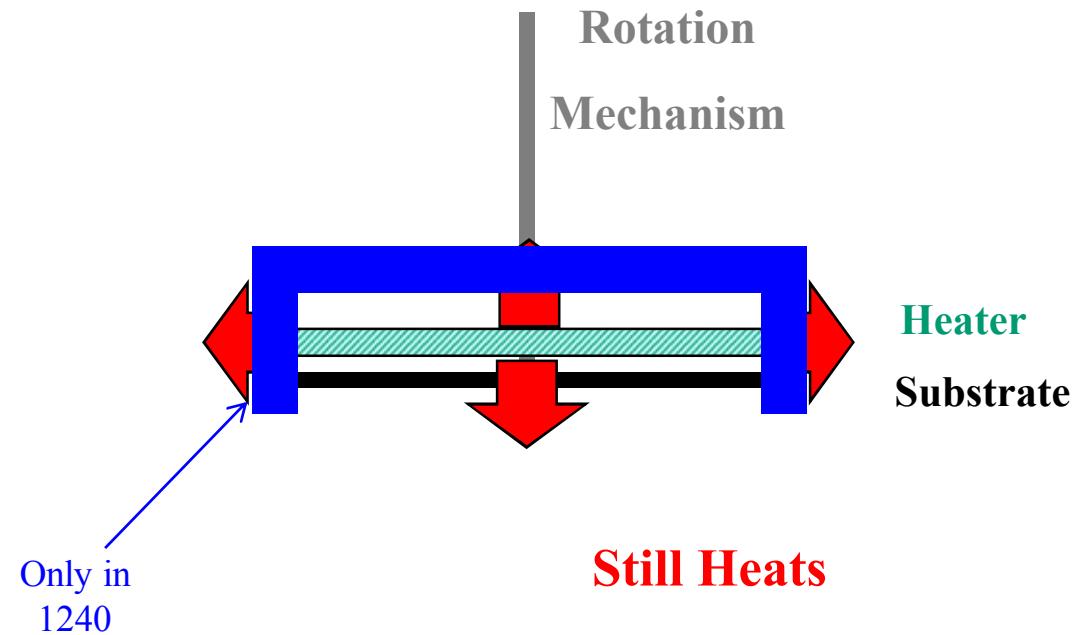
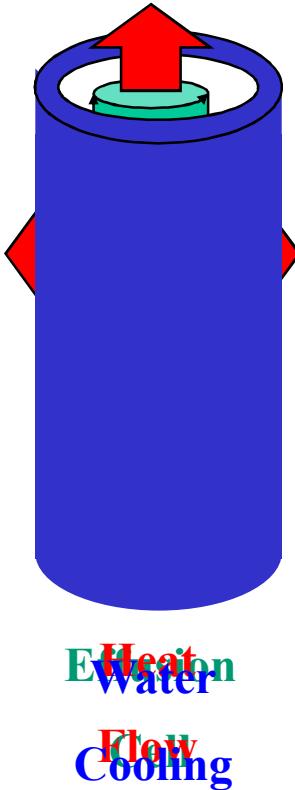


Handling Heat

(To decrease impurities)

Still Heats

- Closed Shutter
- Substrate





1240 Source LN_2 Shrouds

substrate

Positives

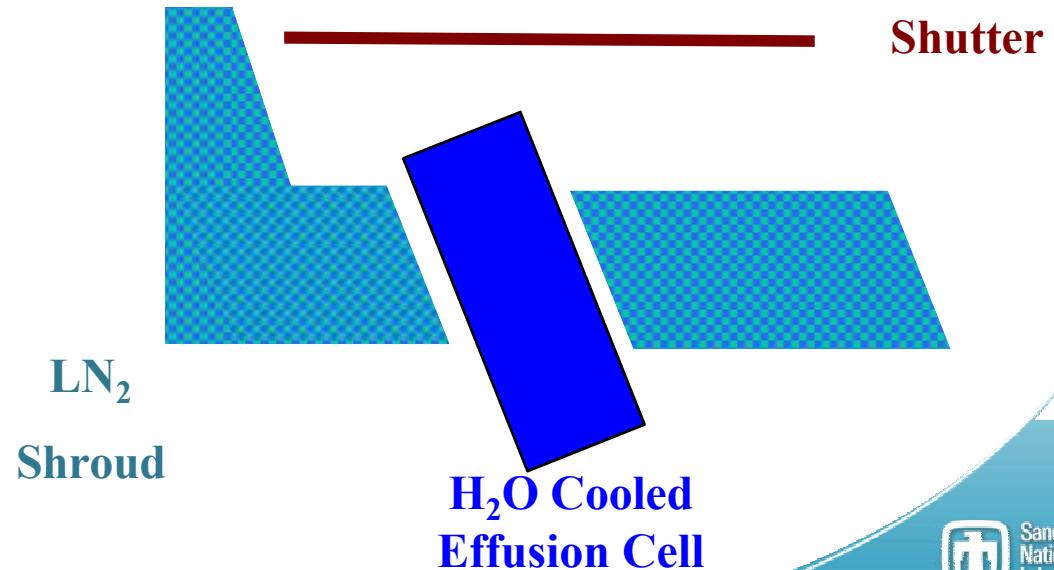
- Angled, “loose” shutter
=> minimal shutter transients
- Heated reflected to LN_2

Negatives

- Solid material build-up near cells
- Liquid (Ga) goes ??

Max Mobility

12 million





Gen20 Source LN_2 Shrouds

Positives

- Bent shutter
=> lowers shutter transients
- Cell behind LN_2
=> protected from flakes
- Heated reflected to LN_2

substrate

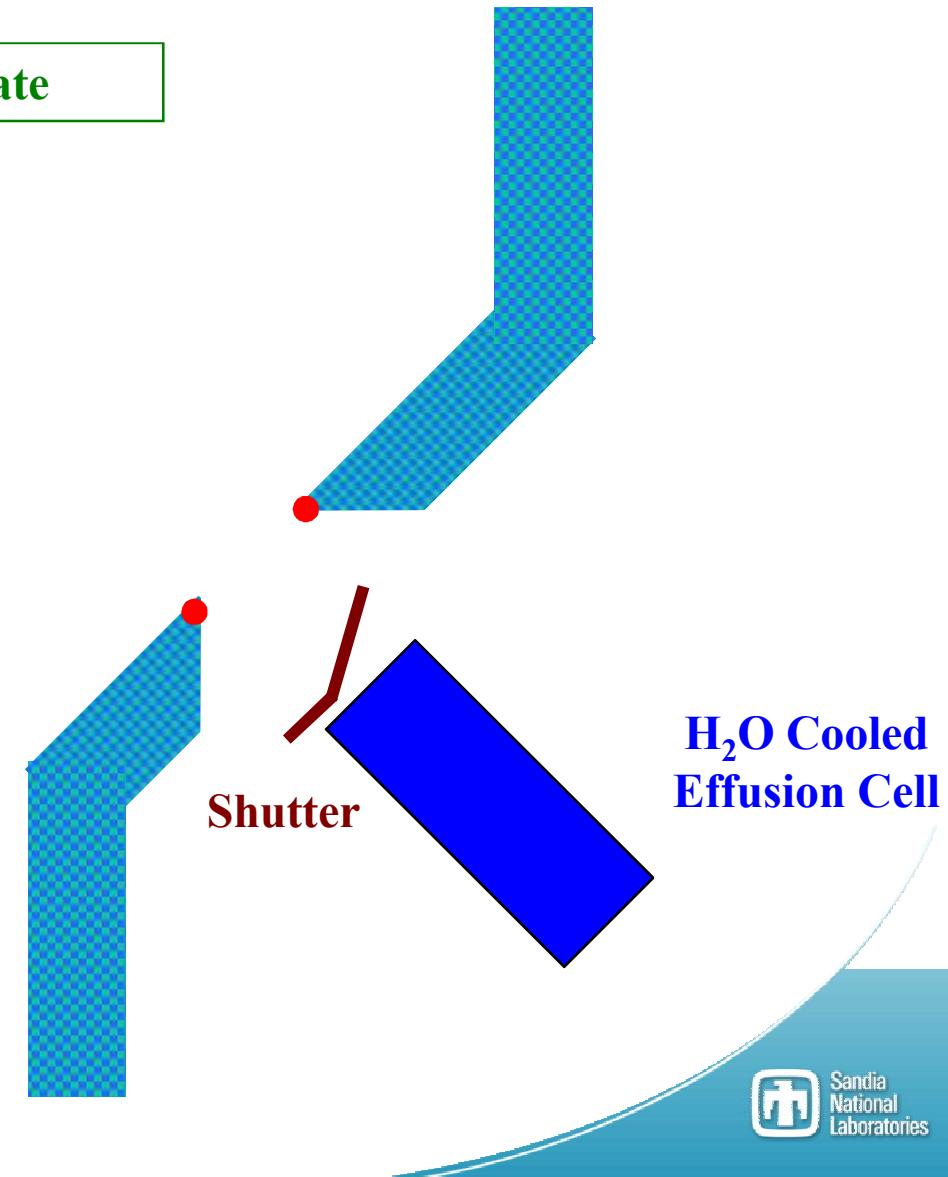
Negatives

- Material build-up above cells
- Liquid (Ga) drips on cell

Max Mobility

2 million

LN_2
Shroud





Which Project is Grown Where?

- Projects type
 - **“High” mobility 2D** electrons and holes for transport
 - **Quantum cascade laser** (QCL) primarily in THz
 - **Other** optical emitters and detectors

1240

GEN20

Either



4" High Mobility Summary

- 4" can not compete with 2" for maximum mobility.
- 4" can grow somewhat high mobility (12 million)
- 4" better than 2" for projects that require a lot of processing.
 - i.e. Gated quantum wires and dots
- Details of design affects optimal device choices and possible research directions.
- Small design details can make a lot of difference

